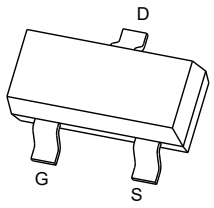
TKBSS84

50V P-Channel MOSFET

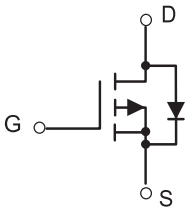
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-50V	1.7Ω@-10V	-0.13A
	1.9Ω@-5V	

SOT-23



Schematic diagram



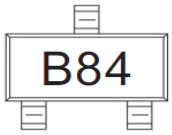
Feature

- Trench Technology MOSFET
- Low Gate Charge

Application

- Load Switch for Portable Devices
- DC/DC Converter

MARKING:



ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	-50	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1]	T_A = 25℃	I_D	-0.13	A
Pulsed Drain Current[2]		I_{DM}	-1.2	A
Power Dissipation[4]	T_A = 25℃	P_D	300	mW
Thermal Resistance from Junction to Ambient[5]		$R_{\theta JA}$	417	℃/W
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain – Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -50V, V_{GS} = 0V			-1	μA
Gate – Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-0.9	-1.4	-2.0	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -0.1A		1.7	5	Ω
		V_{GS} = -4.5V, I_D = -0.1A		1.9	6	
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = -25V, V_{GS} = 0V, f = 1MHz		32.9		pF
Output Capacitance	C_{oss}			5.48		
Reverse Transfer Capacitance	C_{rss}			3.31		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		73		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = -10V, V_{GS} = -10V, I_D = -0.1A		0.62		nC
Gate-source Charge	Q_{gs}			0.13		
Gate-drain Charge	Q_{gd}			0.11		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -30V, V_{GS} = -10V, R_L = 110Ω, R_G = 50Ω		11		ns
Turn-on Rise Time	t_r			6		
Turn-off Delay Ttime	$t_{d(off)}$			19		
Turn-off Fall Ttime	t_f			8		
Source - Drain Diode Characteristics						
Diode Forward Voltage[3]	V_{SD}	V_{GS} = 0V, I_S = -0.1A			-1.2	V

Notes :

1.The maximum current rating is limited by Chip.

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

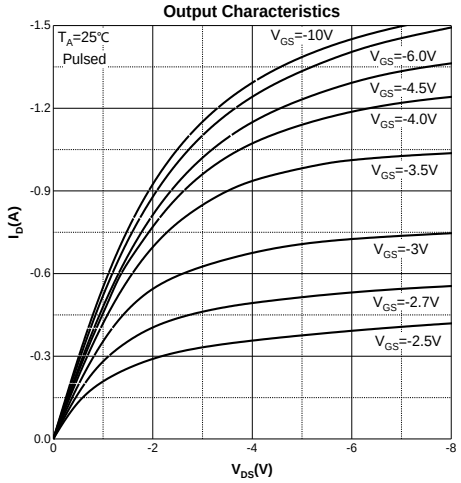
3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

4.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.

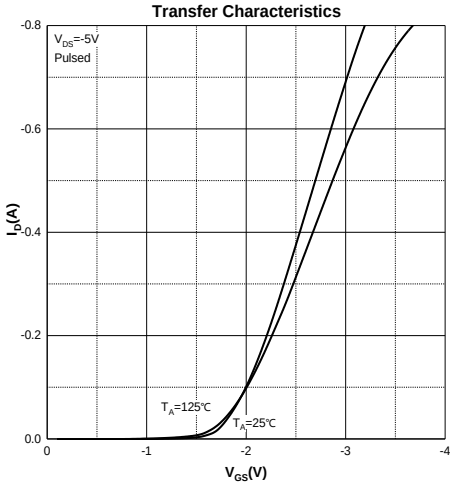
5.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Characteristics

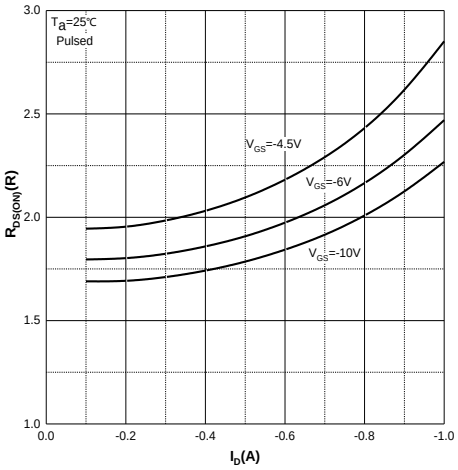
Output Characteristics



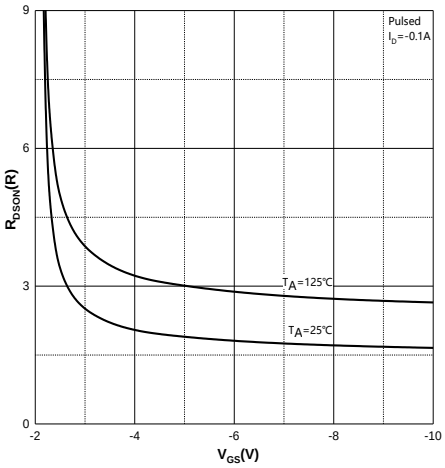
Transfer Characteristics



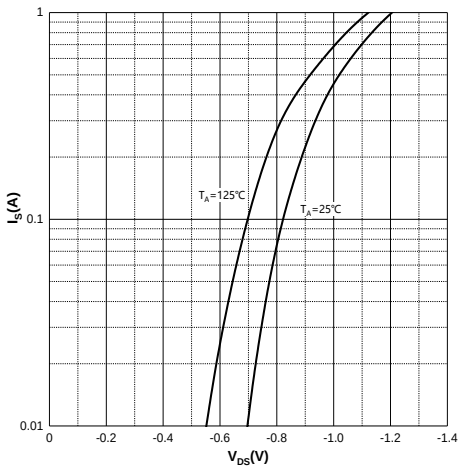
$R_{DS(ON)}$ vs I_D



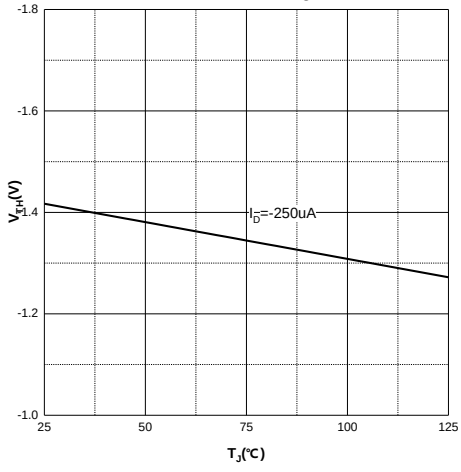
$R_{DS(ON)}$ vs V_{GS}

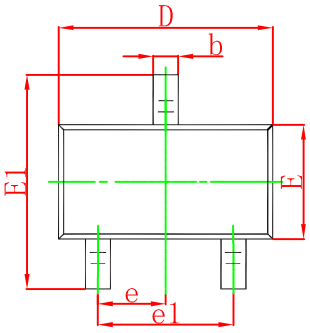


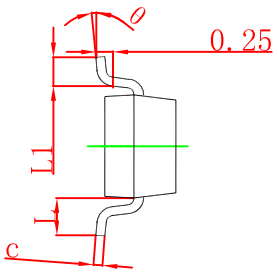
I_S vs V_{SD}

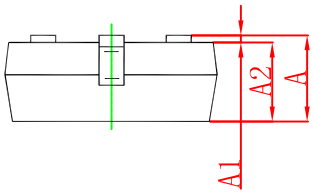


Threshold Voltage



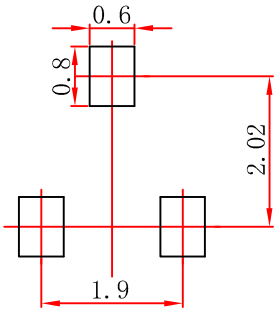






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.